





SN54SLC8T245-SEP SCES946B - FEBRUARY 2022 - REVISED DECEMBER 2023

SN54SLC8T245-SEP 8-Bit Dual-Supply Bus Transceiver With Configurable Voltage **Translation and Tri-State Outputs** 

### 1 Features

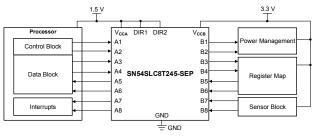
Texas

**INSTRUMENTS** 

- VID V62/22604
- Radiation tolerant:
  - Single event latch-up (SEL) immune up to 43 MeV-cm<sup>2</sup> /mg at 125°C
  - Total ionizing dose (TID) Radiation Lot Acceptance Testing (RLAT) for every wafer lot up to 20 krad(Si)
- Qualified, fully configurable dual-rail design allows each port to operate with a power supply range from 0.65 V to 3.6 V
- Operating temperature from -55°C to +125°C
- ٠ Multiple direction-control pins allows simultaneous up and down translation
- Up to 380 Mbps support when translating from 1.8 V to 3.3 V
- V<sub>CC</sub> isolation feature that effectively isolates both buses in a power-down scenario
- Partial power-down mode to limit backflow current in a power-down scenario
- Latch-up performance exceeds 100 mA per JESD 78, class II
- ESD protection exceeds JESD 22
  - 8000-V human-body model
  - 1000-V charged-device model

## 2 Applications

- Supports low earth orbit (LEO) space applications
- Space radar and communications
- Space satellite payloads



Typical Application Schematic

### **3 Description**

The SN54SLC8T245-SEP device is an 8-bit noninverting bus transceiver that resolves voltage level mismatch between devices operating at the latest voltage nodes (0.7 V, 0.8 V, and 0.9 V) and devices operating at industry standard voltage nodes (1.8 V, 2.5 V, and 3.3 V).

The device operates by using two independent powersupply rails ( $V_{CCA}$  and  $V_{CCB}$ ) that operate as low as 0.65 V. Data pins A1 through A8 are designed to track V<sub>CCA</sub>, which accepts any supply voltage from 0.65 V to 3.6 V. Data pins B1 through B8 are designed to track V<sub>CCB</sub>, which accepts any supply voltage from 0.65 V to 3.6 V.

The SN54SLC8T245-SEP device is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level of the direction-control inputs (DIR1 and DIR2). The output-enable  $(\overline{OE})$  input is used to disable the outputs so the buses are effectively isolated.

The SN54SLC8T245-SEP device is designed so the control pins (DIR and  $\overline{OE}$ ) are referenced to V<sub>CCA</sub>.

This device is fully specified for partial-power-down applications using  $I_{\text{off}}.$  The  $I_{\text{off}}$  circuitry disables the outputs when the device is powered down. This inhibits current backflow into the device which prevents damage to the device.

The  $V_{CC}$  isolation feature is designed so that if either  $V_{CC}$  input supply is below 100 mV, all level shifter outputs are disabled and placed into a highimpedance state.

To put the level shifter I/Os in the high-impedance state during power up or power down, tie  $\overline{OE}$  to V<sub>CCA</sub> through a pullup resistor; the current-sinking capability of the driver determines the minimum value of the resistor.

#### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
SN54SLC8T245-SEP	PW (TSSOP, 24)	7.8 mm × 6.4 mm

For more information, see Section 11. (1)

(2)The package size (length × width) is a nominal value and includes pins, where applicable.





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### **4** Pin Configuration and Functions

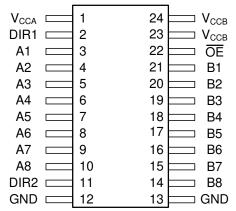


Figure 4-1. PW Package, 24-Pin TSSOP (Top View)

PIN			
NAME	NO.	TYPE <sup>(1)</sup>	DESCRIPTION
A1	3	I/O	Input/output A1. Referenced to V <sub>CCA</sub> .
A2	4	I/O	Input/output A2. Referenced to V <sub>CCA</sub> .
A3	5	I/O	Input/output A3. Referenced to V <sub>CCA</sub> .
A4	6	I/O	Input/output A4. Referenced to V <sub>CCA</sub> .
A5	7	I/O	Input/output A5. Referenced to V <sub>CCA</sub> .
A6	8	I/O	Input/output A6. Referenced to V <sub>CCA</sub> .
A7	9	I/O	Input/output A7. Referenced to V <sub>CCA</sub> .
A8	10	I/O	Input/output A8. Referenced to V <sub>CCA</sub> .
B1	21	I/O	Input/output B1. Referenced to V <sub>CCB</sub> .
B2	20	I/O	Input/output B2. Referenced to V <sub>CCB</sub> .
B3	19	I/O	Input/output B3. Referenced to V <sub>CCB</sub> .
B4	18	I/O	Input/output B4. Referenced to V <sub>CCB</sub> .
B5	17	I/O	Input/output B5. Referenced to V <sub>CCB</sub> .
B6	16	I/O	Input/output B6. Referenced to V <sub>CCB</sub> .
B7	15	I/O	Input/output B7. Referenced to V <sub>CCB</sub> .
B8	14	I/O	Input/output B8. Referenced to V <sub>CCB</sub> .
DIR1	2	I	Direction-control signal 1. Referenced to V <sub>CCA</sub> .
DIR2	11	I	Direction-control signal 2. Referenced to $V_{CCA}$ . Tie to GND to maintain backward compatibility with SN74AVC8T245 device.
	12	_	Ground
GND	13	_	Ground
ŌĒ	22	I	Output Enable. Pull to GND to enable all outputs. Pull to $V_{CCA}$ to place all outputs in high-impedance mode. Referenced to $V_{CCA}$ .
V <sub>CCA</sub>	1	_	A-port supply voltage. $0.65 \text{ V} \le \text{V}_{CCA} \le 3.6 \text{ V}$
M	23	_	B-port supply voltage. $0.65 \text{ V} \le \text{V}_{\text{CCB}} \le 3.6 \text{ V}$
V <sub>CCB</sub>	24	_	B-port supply voltage. $0.65 \text{ V} \le \text{V}_{\text{CCB}} \le 3.6 \text{ V}$

#### Table 4-1. Pin Functions

(1) I = input, O = output



# 5 Specifications

#### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT	
Supply voltage, V <sub>CCA</sub>		-0.5	4.2	V	
Supply voltage, V <sub>CCB</sub>		-0.5	4.2	V	
upply voltage, $V_{CCB}$ uput voltage, $V_{I}$ <sup>(2)</sup> oltage applied to any output the high-impedance or power-off state, $V_{O}$ <sup>(2)</sup> oltage applied to any output in the high or low state, $V_{O}$ <sup>(2) (3)</sup>	I/O ports (A port)	-0.5	4.2		
Input voltage, V <sub>I</sub> <sup>(2)</sup>	I/O ports (B port)	-0.5	4.2	V	
	Control inputs	-0.5	4.2		
Voltage applied to any output	A port	-0.5	4.2	V	
in the high-impedance or power-off state, $V_0$ <sup>(2)</sup>	B port	-0.5	4.2	v	
Supply voltage, V <sub>CCB</sub> Input voltage, V <sub>I</sub> <sup>(2)</sup> Voltage applied to any output	A port	-0.5	V <sub>CCA</sub> + 0.2	V	
	B port	-0.5	V <sub>CCB</sub> + 0.2	v	
Input clamp current, I <sub>IK</sub>	V <sub>1</sub> < 0	-50		mA	
Output clamp current, I <sub>OK</sub>	V <sub>0</sub> < 0	-50		mA	
Continuous output current, I <sub>O</sub>		-50	50	mA	
Continuous current through V <sub>CCA</sub> , V <sub>CCB</sub> , or GND		-100	100	mA	
Junction Temperature, T <sub>J</sub>			150	°C	
Storage temperature, T <sub>stg</sub>		-65	150	°C	

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.2 V maximum if the output current rating is observed.

#### 5.2 ESD Ratings

			VALUE	UNIT
V	ם Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±8000	V
V <sub>(E</sub>		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

		<u> </u>		MIN	MAX	UNIT			
V <sub>CCA</sub>	Supply voltage			0.65	3.6	V			
V <sub>CCB</sub>	Supply voltage			0.65	3.6	V			
			V <sub>CCI</sub> = 0.65 V – 0.75 V	V <sub>CCI</sub> × 0.70					
			V <sub>CCI</sub> = 0.76 V – 1 V	V <sub>CCI</sub> × 0.70					
		Data inputs	V <sub>CCI</sub> = 1.1 V – 1.95 V	V <sub>CCI</sub> × 0.65					
			V <sub>CCI</sub> = 2.3 V – 2.7 V	1.6					
V	High-level input voltage		V <sub>CCI</sub> = 3 V – 3.6 V	2		V			
VIH	nigri-level input voltage		V <sub>CCA</sub> = 0.65 V – 0.75 V	V <sub>CCA</sub> × 0.70					
		Control inputs	V <sub>CCA</sub> = 0.76 V – 1 V	V <sub>CCA</sub> × 0.70					
		(DIR, OE)	V <sub>CCA</sub> = 1.1 V – 1.95 V	V <sub>CCA</sub> × 0.65					
		Referenced to $V_{CCA}$	V <sub>CCA</sub> = 2.3 V – 2.7 V	1.6					
			V <sub>CCA</sub> = 3 V – 3.6 V	2					
			V <sub>CCI</sub> = 0.65 V – 0.75 V		V <sub>CCI</sub> × 0.30				
			V <sub>CCI</sub> = 0.76 V – 1 V		V <sub>CCI</sub> × 0.30				
		Data inputs	V <sub>CCI</sub> = 1.1 V – 1.95 V		V <sub>CCI</sub> × 0.35				
			V <sub>CCI</sub> = 2.3 V – 2.7 V		0.7				
V <sub>IL</sub>	Low-level input voltage		V <sub>CCI</sub> = 3 V – 3.6 V		0.8	v			
۷IL	Low-level input voltage		V <sub>CCA</sub> = 0.65 V – 0.75 V		V <sub>CCA</sub> × 0.30				
		Control inputs	V <sub>CCA</sub> = 0.76 V – 1 V		$V_{CCA} \times 0.30$				
		(DIR, OE)	V <sub>CCA</sub> = 1.1 V – 1.95 V		$V_{CCA} \times 0.35$				
		Referenced to $V_{CCA}$	V <sub>CCA</sub> = 2.3 V – 2.7 V		0.7				
			V <sub>CCA</sub> = 3 V – 3.6 V		0.8				
VI	Input voltage <sup>(3)</sup>		,	0	3.6	V			
V	Output voltage	Active state		0	V <sub>CCO</sub> <sup>(2)</sup>	v			
/ <sub>0</sub>		Tri-state		0	3.6				
Δt/Δv	Input transition rise or fall rate				10	ns/V			
T <sub>A</sub>	Operating free-air temperatur	e		-55	125	°C			
				-					

(1)

 $V_{CCI}$  is the  $V_{CC}$  associated with the input port.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. All unused data inputs of the device must be held at  $V_{CCI}$  or GND for proper device operation. See the *Implications of Slow or Floating* (2) (3) CMOS Inputs application report.

#### **5.4 Thermal Information**

		SN54SLC8T245-SEP	
	THERMAL METRIC	PW (TSSOP)	UNIT
		24 PINS	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	102.9	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	45.9	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	58.2	°C/W
ΨJT	Junction-to-top characterization parameter	6.9	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	57.8	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	°C/W



### **5.5 Electrical Characteristics**

Over recommended operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

I	PARAMETER	TE	ST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	MIN	TYP <sup>(2)</sup> MAX	UNI
			I <sub>OH</sub> = –100 μA	0.7 V – 3.6 V	0.7 V – 3.6 V	V <sub>CCO</sub> – 0.1		
			I <sub>OH</sub> = –50 μA	0.65 V	0.65 V	0.55		1
			I <sub>OH</sub> = –200 μA	0.76 V	0.76 V	0.58		
			I <sub>OH</sub> = –500 μA	0.85 V	0.85 V	0.65		
/ <sub>он</sub>	High-level output voltage	V <sub>I</sub> = V <sub>IH</sub>	I <sub>OH</sub> = -3 mA	1.1 V	1.1 V	0.85		v
	voltage		I <sub>OH</sub> = -6 mA	1.4 V	1.4 V	1.05		
			I <sub>OH</sub> = -8 mA	1.65 V	1.65 V	1.2		
			I <sub>OH</sub> = -9 mA	2.3 V	2.3 V	1.75		
			I <sub>OH</sub> = -12 mA	3 V	3 V	2.3		
			I <sub>OL</sub> = 100 μA	0.7 V – 3.6 V	0.7 V – 3.6 V		0.1	
			I <sub>OL</sub> = 50 μA	0.65 V	0.65 V		0.1	
			I <sub>OL</sub> = 200 μA	0.76 V	0.76 V		0.18	
			I <sub>OL</sub> = 500 μA	0.85 V	0.85 V		0.2	
V <sub>OL</sub>	Low-level output	$V_{I} = V_{IL}$	I <sub>OL</sub> = 3 mA	1.1 V	1.1 V	·	0.25	v
	voltage		$I_{OL} = 6 \text{ mA}$	1.4 V	1.4 V	·	0.35	
			I <sub>OL</sub> = 8 mA	1.65 V	1.65 V	·	0.45	
			I <sub>OL</sub> = 9 mA	2.3 V	2.3 V		0.55	
			I <sub>OL</sub> = 12 mA	3 V	3 V	·	0.7	
1	Input leakage current	Control Inpu V <sub>I</sub> = V <sub>CCA</sub> o	uts (DIR, OE):	0.65 V – 3.6 V	0.65 V – 3.6 V	-1	1	μA
	Partial power	A Port: V <sub>I</sub> or V <sub>O</sub> = 0	) V – 3.6 V	0 V	0 V – 3.6 V	-35	55	
off	down current	B Port: V <sub>I</sub> or V <sub>O</sub> = 0	V – 3.6 V	0 V – 3.6 V	0 V	-35	55	μA
	High-impedance state output	A Port: $V_0 = V_{CCO}$ $\overline{OE} = V_{IH}$	or GND, V <sub>I</sub> = V <sub>CCI</sub> or GND,	3.6 V	3.6 V	-8	8	
oz	current	B Port: $V_0 = V_{CCO}$ $\overline{OE} = V_{IH}$	or GND, V <sub>I</sub> = V <sub>CCI</sub> or GND,	3.6 V	3.6 V	-8	8	μA
				0.65 V – 3.6 V	0.65 V – 3.6 V		40	
CCA	V <sub>CCA</sub> supply current	V <sub>I</sub> = V <sub>CCI</sub> or	GND, I <sub>O</sub> = 0 mA	0 V	3.6 V	-12		μA
				3.6 V	0 V		35	
				0.65  V - 3.6  V	0.65 V – 3.6 V		38	
ССВ	V <sub>CCB</sub> supply current	V <sub>I</sub> = V <sub>CCI</sub> or	GND, I <sub>O</sub> = 0 mA	0 V	3.6 V		35	μA
	_			3.6 V	0 V	-12		
сса <b>+</b> ссв	Combined supply current	V <sub>I</sub> = V <sub>CCI</sub> or	GND, I <sub>O</sub> = 0 mA	0.65 V – 3.6 V	0.65 V – 3.6 V		70	μA
2 <sub>i</sub>	Input capacitance	Control Inpu V <sub>I</sub> = 3.3 V o	uts (DIR, <del>OE</del> ): r GND	3.3 V	3.3 V		4.5	pF
C <sub>io</sub>	Data I/O capacitance		B: V <sub>O</sub> = 1.65 V DC + dBm sine wave	3.3 V	3.3 V		5.7	pF

 $V_{CCO}$  is the  $V_{CC}$  associated with the output port. All typical values are for  $T_A$  = 25°C

(1) (2)



## 5.6 Switching Characteristics, $V_{CCA}$ = 0.7 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

					B-PORT S	UPPLY VO	LTAGE (	V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	-	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	ТҮР	
t Dranagation dalay	Propagation delay	From input A to output B	68	47	34	23	21	21	23	27	ns
t <sub>pd</sub>	Fropagation delay	From input B to output A	67	55	46	32	28	26	25	25	115
		From input OE to output A	100	100	100	100	100	100	100	100	
t <sub>dis</sub>	Disable time	From input $\overline{OE}$ to output B	111	86	73	38	34	34	33	36	ns
+	Enable time	From input OE to output A	105	105	105	105	105	105	105	105	ns
Len		From input OE to output B	127	78	56	39	36	36	39	47	113

### 5.7 Switching Characteristics, V<sub>CCA</sub> = 0.8 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

					B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
+	t Dranagation dalay	From input A to output B	55	38	26	16	14	13	13	14	ns
t <sub>pd</sub>	Propagation delay	From input B to output A	47	38	32	21	17	15	14	14	115
	Disable time	From input OE to output A	71	71	71	71	71	71	71	71	
t <sub>dis</sub>	Disable time	From input OE to output B	105	79	66	32	28	27	25	26	ns
	t <sub>en</sub> Enable time	From input OE to output A	64	64	64	64	64	64	64	64	ns
t <sub>en</sub>		From input $\overline{OE}$ to output B	118	69	47	30	27	26	26	28	115

### 5.8 Switching Characteristics, V<sub>CCA</sub> = 0.9 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

					B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	ТҮР	TYP	TYP	
	Propagation delay	From input A to output B	45	31	21	13	10	9	9	9	ns
t <sub>pd</sub>	Propagation delay	From input B to output A	35	27	23	15	11	10	9	8	
+	Disable time	From input OE to output A	55	55	55	55	55	55	55	55	
t <sub>dis</sub>	Disable time	From input OE to output B	99	74	61	26	23	22	20	20	ns
+		From input OE to output A	41	41	41	41	41	41	41	41	
t <sub>en</sub>	Enable time	From input $\overline{OE}$ to output B	108	63	41	24	20	19	18	19	ns



## 5.9 Switching Characteristics, $V_{CCA}$ = 1.2 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

	Propagation delay     From input A to output       From input B to output     From input Disable time				B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	ТҮР	TYP	TYP	
+ .	Propagation dolay	From input A to output B	33	21	14	8	6	5	5	5	ns
t <sub>pd</sub>	Propagation delay	From input B to output A	24	16	13	8	6	5	4	4	115
+	Disable time	From input $\overline{OE}$ to output A	19	19	19	19	19	19	19	19	20
t <sub>dis</sub>	Disable time	From input OE to output B	92	66	53	20	17	16	14	14	ns
	Enchlo timo	From input OE to output A	19	19	19	19	19	19	19	19	20
t <sub>en</sub>	Enable time	From input OE to output B	96	53	33	17	12	11	10	10	ns

### 5.10 Switching Characteristics, V<sub>CCA</sub> = 1.5 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

					B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	TYP	TYP	TYP	
+	Propagation delay	From input A to output B	29	17	11	6	5	4	4	3	ns
t <sub>pd</sub>	Flopagation delay	From input B to output A	23	14	10	6	5	4	3	3	113
	Disable time	From input OE to output A	15	15	15	15	15	15	15	15	ns
t <sub>dis</sub>	Disable time	From input OE to output B	89	64	50	18	15	15	12	13	115
	Enable time	From input OE to output A	12	12	12	12	12	12	12	12	20
t <sub>en</sub>		From input OE to output B	92	49	29	14	10	8	7	7	ns

## 5.11 Switching Characteristics, $V_{CCA}$ = 1.8 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

			B-PORT SUPPLY VOLTAGE (V <sub>CCB</sub> )								
PARAMETER		TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	YP TYP	TYP	TYP	TYP	TYP	TYP	TYP	
	Drenegation dalay	From input A to output B	28	15	9	5	4	4	3	3	
t <sub>pd</sub>	Propagation delay	From input B to output A	23	13	9	5	4	4	3	2	ns
	Dia abla tira a	From input OE to output A	14	14	14	14	14	14	14	14	
t <sub>dis</sub>	Disable time	From input OE to output B	89	63	49	17	15	14	12	12	ns
	E 11 0	From input OE to output A	9	9	9	9	9	9	9	9	
t <sub>en</sub>	Enable time	From input OE to output B	91	47	28	13	9	7	6	6	ns



## 5.12 Switching Characteristics, V<sub>CCA</sub> = 2.5 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

	Propagation delay     From input A to output B       From input B to output A     From input DE to output       Disable time     From input OE to output				B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	TYP	ТҮР	TYP	TYP	
+ .	Propagation dolay	From input A to output B	27	14	8	4	3	3	2	2	ns
t <sub>pd</sub>	Propagation delay	From input B to output A	26	13	8	5	4	3	2	2	115
	Disable time	From input $\overline{OE}$ to output A	11	11	11	11	11	11	11	11	ns
t <sub>dis</sub>		From input OE to output B	88	62	48	16	13	13	11	11	115
+	Enable time	From input OE to output A	6	6	6	6	6	6	6	6	ne
Len	Enable time	From input $\overline{OE}$ to output B	89	46	26	12	8	7	5	5	ns

### 5.13 Switching Characteristics, V<sub>CCA</sub> = 3.3 V

See Figure 6-1 and Figure 6-2 for test circuit and loading conditions. See Figure 6-3 and Figure 6-4 for measurement waveforms.

					B-POR	T SUPPLY	VOLTAGE	(V <sub>CCB</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V ± 0.05 V	0.8 V ± 0.04 V	0.9 V ± 0.045 V	1.2 V ± 0.1 V	1.5 V ± 0.1 V	1.8 V ± 0.15 V	2.5 V ± 0.2 V	3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	TYP	ТҮР	ТҮР	ТҮР	TYP	
+	Propagation delay	From input A to output B	27	13	8	4	3	2	2	2	ns
t <sub>pd</sub>		From input B to output A	31	14	9	5	3	3	2	2	113
+	Disable time	From input OE to output A	11	11	11	11	11	11	11	11	ns
t <sub>dis</sub>	Disable time	From input OE to output B	87	61	48	16	13	12	11	11	115
+	Enable time	From input OE to output A	5	5	5	5	5	5	5	5	25
t <sub>en</sub>	Enable time	From input OE to output B	89	45	26	11	8	6	5	4	ns

#### **5.14 Operating Characteristics**

 $T_A$  = 25°C, C<sub>L</sub> = 0, R<sub>L</sub> = Open, f = 1 MHz, t<sub>r</sub> = t<sub>f</sub> = 1 ns

	V <sub>CCB</sub> Power dissipation				SUPPLY	VOLTA	GE (V <sub>CCA</sub>	= V <sub>ссв</sub> )			
	PARAMETER	TEST CONDITIONS	0.7 V	0.8 V	0.9 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	UNIT
			TYP	TYP	ΤΥΡ	TYP	TYP	TYP	ΤΥΡ	ΤΥΡ	
		A to B: Outputs Enabled	1.2	1.8	1.8	1.7	1.7	1.7	2	2.5	pF
	dissination	A to B: Outputs Disabled	1.1	1.8	1.8	1.7	1.7	1.7	2	2.1	pF
C <sub>pdA</sub>	capacitance per	B to A: Outputs Enabled	9.3	11.8	11.8	12	12.2	13	16.4	18.1	pF
		B to A: Outputs Disabled	2.6	1.2	1.1	1.2	1.2	1.3	1.6	3.9	pF
		A to B: Outputs Enabled	9.3	11.7	11.8	11.9	12.2	12.9	16.3	18	pF
	005	A to B: Outputs Disabled	2.6	11.7	11.8	11.9	12.2	12.9	16.3	3.9	pF
CpdB	transceiver	B to A: Outputs Enabled	1.2	1.8	1.8	1.7	1.7	1.7	2	2.5	pF
		B to A: Outputs Disabled	1.1	1.8	1.8	1.7	1.7	1.7	2	2.1	pF

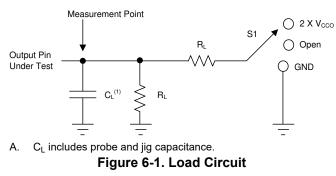
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### **6** Parameter Measurement Information

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f =1 MHz
- $Z_0 = 50 \Omega$
- dv / dt ≤ 1 ns/V

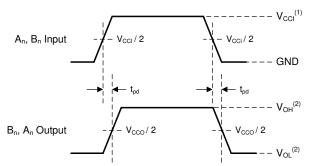


Para	meter	V <sub>cco</sub>	$R_L$	$C_{L}$	S1	$V_{\text{TP}}$
t	pd	1.1 V - 3.6 V	2 kΩ	15 pF	Open	N/A
	pu	0.65 V - 0.95 V	20 kΩ	15 pF	Open	N/A
		3 V - 3.6 V	2 kΩ	15 pF	$2 X V_{CCO}$	0.3 V
. (1)	. (1)	1.65 V - 2.7 V	2 kΩ	15 pF	$2 X V_{CCO}$	0.15 V
t <sub>en</sub> ,	$t_{en}^{(1)},t_{dis}^{(1)}$	1.1 V - 1.6 V	2 kΩ	15 pF	$2 X V_{CCO}$	0.1 V
		0.65 V - 0.95 V	20 kΩ	15 pF	$2 X V_{CCO}$	0.1 V
		3 V - 3.6 V	2 kΩ	15 pF	GND	0.3 V
ten <sup>(2)</sup>	$t_{en}^{(2)},  {t_{dis}}^{(2)}$	1.65V - 2.7 V	2 kΩ	15 pF	GND	0.15 V
ven	-010	1.1 V - 1.6 V	2 kΩ	15 pF	GND	0.1 V
		0.65 V - 0.95 V	20 kΩ	15 pF	GND	0.1 V

A. Output waveform on the conditions that input is driven to a valid Logic Low.

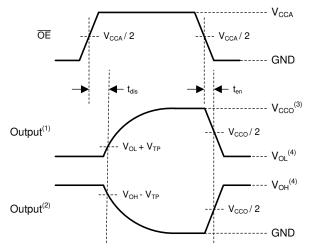
B. Output waveform on the condition that input is driven to a valid Logic High.

#### Figure 6-2. Load Circuit Conditions



- A.  $V_{CCI}$  is the supply pin associated with the input port.
- B.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels with specified R<sub>L</sub>, C<sub>L</sub>, and S<sub>1</sub>.

#### Figure 6-3. Propagation Delay



- A. Output waveform on the condition that input is driven to a valid Logic Low.
- B. Output waveform on the condition that input is driven to a valid Logic High.
- C. V<sub>CCO</sub> is the supply pin associated with the output port.
- D.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels with specified R\_L,  $C_L, \, \text{and} \, S_1.$

Figure 6-4. Enable Time And Disable Time

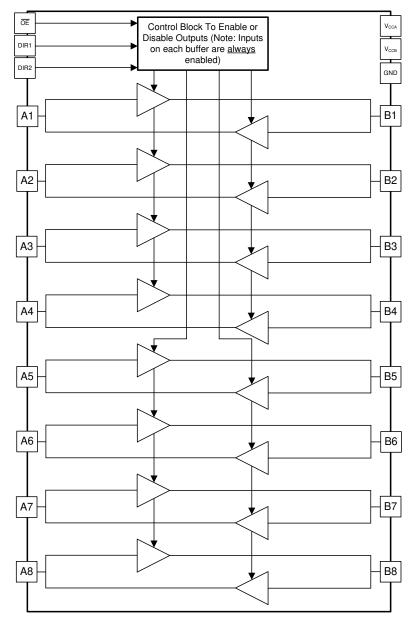


### 7 Detailed Description

### 7.1 Overview

The SN54SLC8T245-SEP device is an 8-bit, dual-supply non-inverting transceiver with bidirectional voltage level translation. The I/O pins labeled with A and the control pins (DIR1, DIR2, and  $\overline{OE}$ ) are supported by V<sub>CCA</sub>, and the I/O pins labeled with B are supported by V<sub>CCB</sub>. The A port and the B port are able to accept I/O voltages ranging from 0.65 V to 3.6 V.

#### 7.2 Functional Block Diagram





#### 7.3 Feature Description

#### 7.3.1 Up-Translation and Down-Translation From 0.65 V to 3.6 V

Both supply pins are configured from 0.65 V to 3.6 V, which makes the device suitable for translating between any of the low voltage nodes (0.7 V, 0.8 V, 0.9 V, 1.2 V, 1.8 V, 2.5 V, and 3.3 V).

#### 7.3.2 Multiple Direction Control Pins

Two control pins are used to configure the 8 data I/Os. I/O channels 1 through 4 are grouped together and I/O channels 5 through 8 are banked together. The benefit of this is to permit simultaneous up-translation and down-translation within one device. This eliminates the need for multiple devices, where each device can only provide up-translation or down-translation sequentially. Simultaneous up and down translation is supported when both  $V_{CCA}$  and  $V_{CCB}$  are at least 1.40 V.

#### 7.3.3 I<sub>off</sub> Supports Partial-Power-Down Mode Operation

This feature is to limit the leakage current of an I/O pin being driven to a voltage as large as 3.6 V while having its corresponding power supply rail powered down. This is represented by the I<sub>off</sub> parameter in the *Electrical Characteristics* table.

#### 7.4 Device Functional Modes

All control inputs are referenced to  $V_{CCA}$  and must be driven to a valid Logic High or Logic Low (that is, not floating) for proper device operation and to prevent excessive power consumption. Table 7-1 summarizes the possible modes of device operation based on the configuration of the control inputs.

	CONTROL INPUTS(1	)	SIGNAL DIRECTION									
ŌĒ	DIR1	DIR2	Bits 1:4	Bits 5:8								
Н	X	X X Disabled (Hi-Z)										
L	L	L	B to	A C								
L	L	Н	B to A	A to B								
L	Н	L A to B										
L	Н	Н	A to B	B to A								

#### Table 7-1. Function Table

(1) Input circuits of the data I/Os are always active and must be driven to a valid logic level.



### 8 Application and Implementation

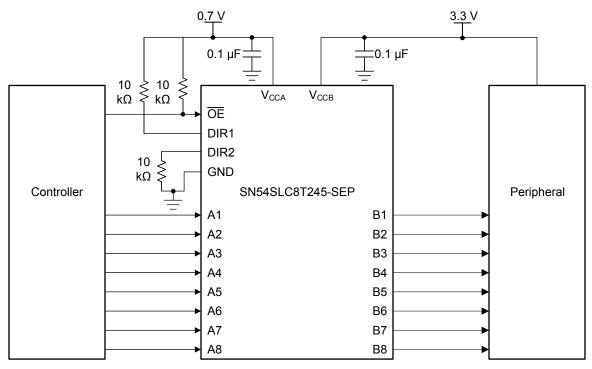
#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 8.1 Application Information

The SN54SLC8T245-SEP device can be used in level-translation applications for interfacing devices or systems operating at different voltage nodes. Figure 8-1 depicts an application in which the SN54SLC8T245-SEP device is up-translating a 0.7 V input to a 3.3 V output to interface between a system controller and a peripheral device.

#### **8.2 Typical Application**



**Figure 8-1. Typical Application Schematic** 



#### 8.2.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

Table 8-1. Desig	gn Parameters
DESIGN PARAMETERS	EXAMPLE VALUE
Input voltage range	0.65 V to 3.6 V
Output voltage range	0.65 V to 3.6 V

#### 8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN54SLC8T245-SEP device to determine the input voltage range. For a valid logic high, the value must exceed the V<sub>IH</sub> of the input port. For a valid logic low, the value must be less than the  $V_{IL}$  of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN54SLC8T245-SEP device is driving to determine the output voltage range.

#### 8.2.3 Application Curve

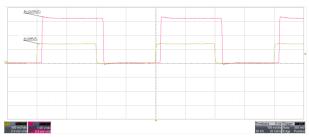


Figure 8-2. Translation Up (0.7 V to 3.3 V) at 2.5 MHz

#### 8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. There are no additional requirements for power supply sequencing.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices. For more information regarding the power up glitch performance of level translators, see the Power Sequencing for AXC Family of Devices application report.



### 8.4 Layout

#### 8.4.1 Layout Guidelines

To device reliability, follow common printed-circuit board layout guidelines:

- Use bypass capacitors on power supplies.
- Use short trace lengths to avoid excessive loading.
- Place pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.

#### 8.4.2 Layout Example

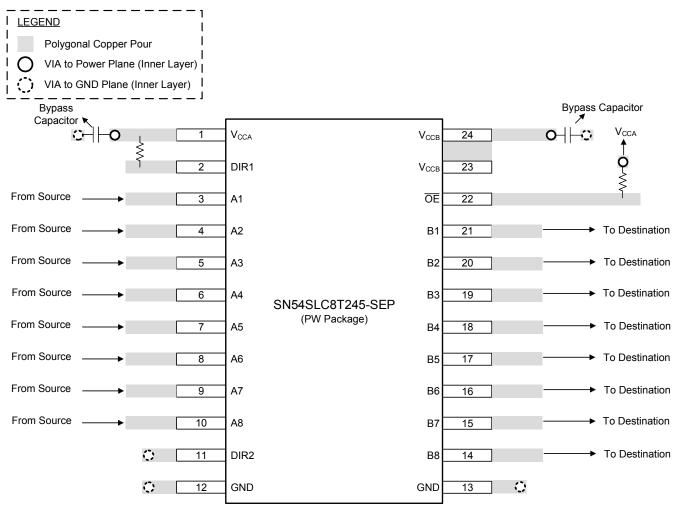


Figure 8-3. SN54SLC8T245-SEP Device Layout Example



### 9 Device and Documentation Support

#### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

• Texas Instruments, Implications of Slow or Floating CMOS Inputs application report

#### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 9.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 9.4 Trademarks

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#### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### **10 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	Changes from Revision A (September 2022) to Revision B (December 2023)	Page
•	Updated the Package Information table to include package lead size	1
•	Updated the Translation Up (0.7 V to 3.3 V) at 2.5 MHz figure	
_		

Changes from Revision	on * (February 2022)	to Revision A (September 2022)	Page

#### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



#### **PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
SN54SLC8T245PWTSEP	Active	Production	TSSOP (PW)   24	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	SLC8T245E
V62/22604-01XE	Active	Production	TSSOP (PW)   24	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	See	SLC8T245E
							SI	N54SLC8T245PWTSEI	

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN54SLC8T245PWTSEP	TSSOP	PW	24	250	180.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1



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# PACKAGE MATERIALS INFORMATION

5-Dec-2023



*All	dimensions	are	nominal
------	------------	-----	---------

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN54SLC8T245PWTSEP	TSSOP	PW	24	250	210.0	185.0	35.0

# **PW0024A**



# **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0024A

# **EXAMPLE BOARD LAYOUT**

### TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0024A

# **EXAMPLE STENCIL DESIGN**

### TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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